DS64EV400 Programmable Quad Equalizer



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General Description

The DS64EV400 programmable quad equalizer provides compensation for transmission medium losses and reduces the medium-induced deterministic jitter for four NRZ data channels. The DS64EV400 is optimized for operation up to 10 Gbps for both cables and FR4 traces. Each equalizer channel has eight levels of input equalization that can be programmed by three control pins, or individually through a Serial Management Bus (SMBus) interface.

The equalizer supports both AC and DC-coupled data paths for long run length data patterns such as PRBS-31, and balanced codes such as 8b/10b. The device uses differential current-mode logic (CML) inputs and outputs, and is available in a 7 mm x 7 mm 48-pin leadless LLP package. Power is supplied from either a 2.5V or 3.3V supply.

Features

- Equalizes up to 24 dB loss at 10 Gbps
- Equalizes up to 22 dB loss at 6.4 Gbps
- 8 levels of programmable equalization
- Settable through control pins or SMBus interface
- Operates up to 10 Gbps with 30" FR4 traces
- Operates up to 6.4 Gbps with 40" FR4 traces
- 0.175 UI residual deterministic jitter at 6.4 Gbps with 40" FR4 traces
- Single 2.5V or 3.3V power supply
- Signal Detect for individual channels
- Standby mode for individual channels
- Supports AC or DC-Coupling with wide input commonmode
 - Low power consumption: 375 mW Typ at 2.5V
- Small 7 mm x 7 mm 48-pin LLP package
- 9 kV HBM ESD
- -40 to 85°C operating temperature range

Тх ASIC/FPGA High Speed I/O DS64EV400 R OUT IN Switch Fabric Card Backplane/Cable Sub-system Line Card Тx ASIC/FPGA High Speed I/O DS64EV400 R OUT IN 30032024 © 2007 National Semiconductor Corporation 300320

Simplified Application Diagram

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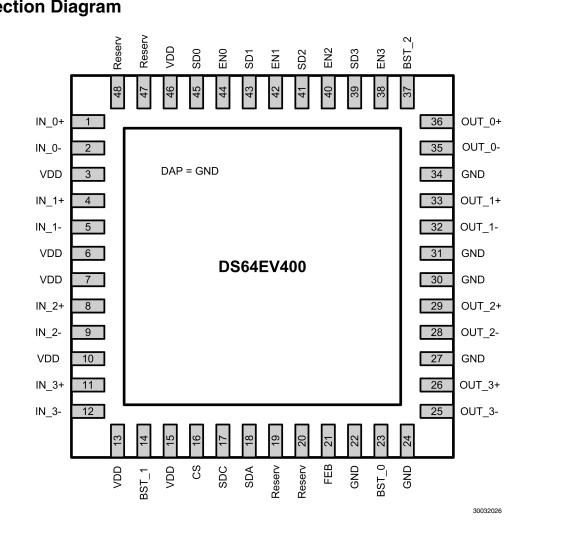
Pin Descriptions

Pin Name	Pin Number	I/O, Type	Description
HIGH SPEED	DIFFERENT	AL I/O	•
IN_0+ IN_0-	1 2	I, CML	Inverting and non-inverting CML differential inputs to the equalizer. An on-chip 100Ω terminating resistor is connected between IN_0+ and IN_0
IN_1+ IN_1-	4 5	I, CML	Inverting and non-inverting CML differential inputs to the equalizer. An on-chip 100Ω terminating resistor is connected between IN_1+ and IN_1
IN_2+ IN_2-	8 9	I, CML	Inverting and non-inverting CML differential inputs to the equalizer. An on-chip 100Ω terminating resistor is connected between IN_2+ and IN_2
IN_3+ IN_3-	11 12	I, CML	Inverting and non-inverting CML differential inputs to the equalizer. An on-chip 100Ω terminating resistor is connected between IN_3+ and IN_3
OUT_0+ OUT_0-	36 35	O, CML	Inverting and non-inverting CML differential outputs from the equalizer. An on-chip 50 Ω terminating resistor connects OUT_0+ to V _{DD} and OUT_0- to V _{DD} .
OUT_1+ OUT_1-	33 32	O, CML	An on-chip 50 Ω terminating resistor connects OUT_1+ to V _{DD} and OUT_1- to V _{DD} .
OUT_2+ OUT_2-	29 28	O, CML	Inverting and non-inverting CML differential outputs from the equalizer. An on-chip 50Ω terminating resistor connects OUT_2+ to V _{DD} and OUT_2- to V _{DD} .
OUT_3+ OUT_3-	26 25	O, CML	Inverting and non-inverting CML differential outputs from the equalizer. An on-chip 50Ω terminating resistor connects OUT_3+ to V _{DD} and OUT_3- to V _{DD} .
EQUALIZATI	ON CONTRO	L	
BST_2 BST_1 BST_0	37 14 23	I, CMOS	BST_2, BST_1, and BST_0 select the equalizer strength for EQ channel 1. BST_2 is internally pulled high. BST_1 and BST_0 are internally pulled low.
DEVICE CON	ITROL		
EN0	44	I, CMOS	Enable Equalizer Channel 0 input. When held High, normal operation is selected. When held Low, standby mode is selected. EN is internally pulled High.
EN1	42	I, CMOS	Enable Equalizer Channel 1 input. When held High, normal operation is selected. When held Low, standby mode is selected. EN is internally pulled High.
EN2	40	I, CMOS	Enable Equalizer Channel 2 input. When held High, normal operation is selected. When held Low, standby mode is selected. EN is internally pulled High.
EN3	38	I, CMOS	Enable Equalizer Channel 3 input. When held High, normal operation is selected. When held Low, standby mode is selected. EN is internally pulled High.
FEB	21	I, CMOS	Force External Boost. When held high, the equalizer boost setting is controlled by BST_[2:0] pins. When held low, the equalizer boost setting is controlled by SMBus (see Table 1) control pins. FEB is internally pulled High.
SD0	45	O, CMOS	Equalizer Channel 0 Signal Detect Output. Produces a High when signal is detected.
SD1	43	O, CMOS	Equalizer Channel 1 Signal Detect Output. Produces a High when signal is detected.
SD2	41	O, CMOS	Equalizer Channel 2 Signal Detect Output. Produces a High when signal is detected.
SD3	39	O, CMOS	Equalizer Channel 3 Signal Detect Output. Produces a High when signal is detected.
POWER			
V _{DD}	3, 6, 7, 10, 13, 15, 46	Power	$V_{DD} = 2.5V \pm 5\%$ or $3.3V \pm 10\%$. V_{DD} pins should be tied to V_{DD} plane through low inductance path. A 0.01µF bypass capacitor should be connected between each V_{DD} pin to GND planes
GND	22, 24, 27, 30, 31, 34	Power	Ground reference. GND should be tied to a solid ground plane through a low impedance path.
Exposed Pad	PAD	Power	Ground reference. The exposed pad at the center of the package must be connected to ground plane of the board.

Pin Name	Pin Number	I/O, Type	Description
SERIAL MAN	AGEMENT B	US (SMBus)	INTERFACE CONTROL PINS
SDA	18	I, CMOS	Data input. Internally pulled high.
SDC	17	I, CMOS	Clock input. Internally pulled high.
CS	16	I, CMOS	Chip select. When held high, access to the equalizer SMBus registers are enabled. When held low, access to the equalizer SMBus registers are disabled. CS is internally gated with SDC.
OTHER			
Reserv	19, 20		Reserved. Do not connect.
	47, 48		

Note: I = Input O = Output

Connection Diagram



DS64EV400

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V _{DD})	-0.5V to +4.0V
CMOS Input Voltage	-0.5V + 4.0V
CMOS Output Voltage	-0.5V to 4.0V
CML Input/Output Voltage	-0.5V to 4.0V
Junction Temperature	+150°C
Storage Temperature	–65°C to +150°C
Lead Temperature (Soldering, 4 Seconds)	+260°C

ESD Rating	
HBM, 1.5 kΩ, 100 pF	>9 kV
CML Inputs	>250V
Thermal Resistance	
θ _{JA} , No Airflow	30°C/W

Recommended Operating Conditions

	Min	Тур	Max	Units
Supply Voltage				
V _{DD2.5} to GND	2.375	2.5	2.625	V
V _{DD3.3} to GND	3.0	3.3	3.6	V
Ambient Temperature	-40	25	+85	°C

Electrical Characteristics

Over recommended operating supply and temperature ranges with default register settings unless other specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
POWER					•	
P	Power Supply Consumption	Device Enabled, V _{DD3.3}		490	700	mW
Symbol Parameter POWER Power Supply Consum P Power Supply Consum P Power Supply Consum N Supply Noise Tolerand (Note 4) LVTTL DC SPECIFICATIONS V _{IH} High Level Input Voltage V _{IL} Low Level Input Voltage V _{OH} High Level Output Volt IN Input Current I _{IN-P} Input Leakage Current Internal Pull-Down/Up SIGNAL DETECT SDH Signal Detect High SDL Signal Detect Low CML RECEIVER INPUTS (IN_n+, IN_		EN0 — EN3 = Low, V _{DD3.3}			100	mW
Р	Power Supply Consumption	ConditionsMinTypMaxDevice Enabled, $V_{DD3,3}$ 490700 $NO - EN3 = Low, V_{DD2,5}$ 360490 $NO - EN3 = Low, V_{DD2,5}$ 300 $O Hz - 100 Hz$ 100 $O Hz - 100 Hz$ 100 $O Hz - 100 Hz$ 40 $O Hz - 3.2 GHz$ 10 $V_{DD2,5}$ 1.6 $V_{DD2,5}$ 0.8 $O Hz - 3.2 GHz$ 0.8 $V_{DD2,5}$ 1.6 V_{DD} -0.3 $O Hz - 3.2 GHz$ 0.8 $V_{DD2,5}$ 2.0 $O_{D1} = -3mA, V_{DD2,5}$ 2.0 $O_{D1} = 3mA$ 0.4 $V_{N} = V_{DD}$ +15 $V_{N} = V_{DD}$ +15 $V_{N} = V_{DD}$,-20 $vith$ internal pull-down resistors80 $V_{N} = V_{DD}$,-20 $vith$ internal pull-up resistors40 $V_{D} = Sert SD, 6.4 Gbps$ 40Differential measurement at point a120 $Pigure 1$) $CC-Coupled$ Requirement Differential measurement at point A400	mW			
				30		ax Units 00 mW 00 mW 90 mV _{P-P} 90 V 91 μA 92 μA 94 μA 95 mV _{P-P} 96 mV _{P-P} 97 mV _{P-P}
N	Power Supply ConsumptionDevice Enabled, $V_{DD3,3}$ 490Power Supply ConsumptionDevice Enabled, $V_{DD2,5}$ 360Power Supply Noise ToleranceDevice Enabled, $V_{DD2,5}$ 30Supply Noise Tolerance50 Hz – 100 Hz100(Note 4)100 Hz100 Hz100 Hz – 10 MHz40100 Hz – 3.2 GHz10PECIFICATIONSHigh Level Input Voltage $V_{DD3,3}$ Low Level Input Voltage $I_{OH} = -3mA, V_{DD3,3}$ 2.4Ich = -3mA, $V_{DD2,5}$ 2.010Low Level Output Voltage $I_{OH} = -3mA, V_{DD3,3}$ 2.4Input Current $V_{IN} = V_{DD}$ 10VIN = GND-1510Input Leakage Current with Internal Pull-Down/Up Resistors $V_{IN} = V_{DD}$, with internal pull-down resistors-20Signal Detect HighDefault input signal level to de- assert SD, 6.4 Gbps80Signal Detect LowDefault input signal level to de- assert SD, 6.4 Gbps40EER INPUTS (IN_n+, IN_n- Input Threshold VoltageInput Threshold VoltageDifferential measurement at point B 		mV _{P-F}			
$\begin{tabular}{ c c c c c c } \hline Power Supply Consumption & Device Enabled, V_{DD3,3} & 490 & EN0 - EN3 = Low, V_{DD3,3} & 490 & EN0 - EN3 = Low, V_{DD3,3} & 490 & EN0 - EN3 = Low, V_{DD2,5} & 360 & EN0 - EN3 = Low, V_{DD2,5} & 30 & N & Supply Noise Tolerance & 50 Hz - 100 Hz & 100 & Hz & $						
		10 MHz – 3.2 GHz		10		
VTTL DC S	PECIFICATIONS	• • •				
И _Н	High Level Input Voltage	V _{DD3.3}	2.0		V _{DD}	V
			1.6			V
/ ₁₁	Low Level Input Voltage	552.5	-0.3			V
		$I_{OH} = -3mA, V_{DD3,3}$	2.4			v
OIT	5 1 5					v
	Low Level Output Voltage				0.4	· · ·
					+15	
			-15			
	Input Leakage Current with				±120	μ <u>η</u>
IN IN-P		1 1			120	μΑ
		· · · · ·	-20			
		==				μA
SIGNAL DET	ГЕСТ	<u> </u>				
SDH	Signal Detect High	Default input signal level to assert				
	5			80		mv _{P-F}
SDL	Signal Detect Low	Default input signal level to de-		40		mW mW mW mW mW mW mV _{P-P} mV _{P-P} mV _{P-P} v v v v v v v v v v v mA μA μA mV _{P-P} mV _{P-P} mV _{P-P} mV _{P-P}
		assert SD, 6.4 Gbps		40		IIIV _{P-F}
CML RECEIN	/ER INPUTS (IN_n+, IN_n-			-	-	
V _{INTRE}	Input Threshold Voltage					
				120		mV _{P-P}
V _{IN}	Input Voltage Swing					
			400		1600	mV _{P-F}
						•P-P
		(Figure 1)				

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V _{DDTX}	Supply Voltage of Transmitter to EQ	DC-Coupled Requirement (Note 9)	1.6		V _{DD}	V
V _{ICMDC}	Input Common-Mode Voltage	DC-Coupled Requirement Differential measurement at point A (Figure 1) (Note 7)	V _{DDTX} – 0.8		V _{DDTX} - 0.2	v
٦ _{LI}	Differential Input Return Loss	100 MHz – 3.2 GHz, with fixture's effect de-embedded		10		dB
R _{IN}	Input Resistance	Differential across IN_n+ and IN_n-	85	100	115	Ω
CML OUTPU	TS (OUT_n+, OUT_n-				• • •	
Vo	Output Voltage Swing	Differential measurement with OUT_n+ and OUT_n- terminated by 50Ω to GND AC-Coupled (Figure 2)	500		725	mV _{P-P}
V _{осм}	Output Common-Mode Voltage	Single-ended measurement DC- Coupled with 50Ω terminations (Note 7)	V _{DD} – 0.2		V _{DD} – 0.1	V
R, t _F	Transition Time	20% to 80% of differential output voltage, measured within 1" from output pins (Figure 2) (Note 7)	25		45	ps
٦ ₀	Output Resistance	Single-ended to V _{DD}	42	50	58	Ω
R _{LO}	Differential Output Return Loss	100 MHz – 3.2 GHz, with fixture's effect de-embedded. IN_n+ = static high		10		dB
PLHD	Differential Low to High Propagation Delay	Propagation delay measurement at 50% $\rm V_O$ between input to output,		240		ps
PHLD	Differential High to Low Propagation Delay	100 Mbps (Figure 3) (Note 7)		240		ps
CCSK	Inter Pair Channel to Channel Skew	Difference in 50% crossing between channels		7		ps
EQUALIZATI	ON					
DJ1	Residual Deterministic Jitter at 10 Gbps	30" of 6 mil microstrip FR4, EQ Setting 0x06, PRBS-7 (2 ⁷ -1) pattern (Note 6)		0.20		UI _{P-P}
DJ2	Residual Deterministic Jitter at 6.4 Gbps	40" of 6 mil microstrip FR4, EQ Setting 0x06, PRBS-7 (2 ⁷ -1) pattern (Note 5, 6)		0.17	0.26	UI _{P-P}
DJ3	Residual Deterministic Jitter at 5 Gbps	40" of 6 mil microstrip FR4, EQ Setting 0x07, PRBS-7 (2 ⁷ -1) pattern (Note 5, 6)		0.12	0.20	UI _{P-P}
DJ4	Residual Deterministic Jitter at 2.5 Gbps	40" of 6 mil microstrip FR4, EQ Setting 0x07, PRBS-7 (2 ⁷ -1) pattern (Note 5, 6)		0.1	0.16	UI _{P-P}
RJ	Random Jitter	(Note 7, 8)		0.5	1	psrms

Symbol	Parameter	Conditions	Min	Тур	Max	Units
SIGNAL DET	ECT and ENABLE TIMING					
t _{ZISD}	TRI-STATE to input SD Delay	Propagation delay measurement		35		ns
t _{IZSD}	Input to Tri-Sate SD Delay	at V _{IN} to SD output, V _{IN} = 800 mV _{P-P} , 100 Mbps, 40" of 6 mil microstrip FR4 (Figure 1, 4) (Note 7)		400		ns
t _{OZED}	EN TRI-STATE to Output Delay	Propagation delay measurement		150		ns
t _{ZOED}	EN Output to TRI-STATE Delay	at EN input to V_O , $V_{IN} = 800 \text{ mV}_{P}$ P, 100 Mbps, 40" of 6 mil microstrip FR4 (Figure 1, 4) (Note 7)		5		ns

Note 1: "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur, including inoperability and degradation of device reliability and/or performance. Functional operation of the device and/or non-degradation at the Absolute Maximum Ratings or other conditions beyond those indicated in the Recommended Operating Conditions is not implied. The Recommended Operating Conditions indicate conditions at which the device is functional and the device should not be operated beyond such conditions. Absolute Maximum Numbers are guaranteed for a junction temperature range of -40°C to +125°C. Models are validated to Maximum Operating Voltages only.

Note 2: Typical values represent most likely parametric norms at V_{DD} = 3.3V or 2.5V, T_A = 25°C., and at the Recommended Operation Conditions at the time of product characterization and are not guaranteed.

Note 3: The Electrical Characteristics tables list guaranteed specifications under the listed Recommended Operating Conditions except as otherwise modified or specified by the Electrical Characteristics Conditions and/or Notes. Typical specifications are estimations only and are not guaranteed.

Note 4: Allowed supply noise (mV_{P-P} sine wave) under typical conditions.

Note 5: Specification is guaranteed by characterization at optimal boost setting and is not tested in production.

Note 6: Deterministic jitter is measured at the differential outputs (point C of Figure 1), minus the deterministic jitter before the test channel (point A of Figure 1). Random jitter is removed through the use of averaging or similar means.

Note 7: Measured with clock-like {11111 00000} pattern.

Note 8: Random jitter contributed by the equalizer is defined as sqrt $(J_{OUT}^2 - J_{IN}^2)$. J_{OUT} is the random jitter at equalizer outputs in ps-rms, see point C of Figure 1; J_{IN} is the random jitter at the input of the equalizer in ps-rms, see point B of Figure 1.

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Electrical Characteristics — Serial Management Bus Interface

Over recommended operating supply and temperature ranges unless other specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
SERIAL BUS	INTERFACE DC SPECIFICATIONS	6	•			•
V _{IL}	Data, Clock Input Low Voltage				0.8	V
V _{IH}	Data, Clock Input High Voltage		2.1		V _{DD}	V
I _{PULLUP}	Current Through Pull-Up Resistor or Current Source		4			mA
V _{DD}	Nominal Bus Voltage		2.375		3.6	V
I _{LEAK-Bus}	Input Leakage Per Bus Segment	(Note 9)	-200		+200	μA
I LEAK-Pin	Input Leakage Per Device Pin			-15		μA
CI	Capacitance for SDA and SDC	(Note 9, 10)			10	pF
R _{TERM}	Termination Resistance	V _{DD3.3} , (Note 9, 10, 11)		2000		Ω
		V _{DD2.5} , (Note 9, 10, 11)		1000		Ω
SERIAL BUS	INTERFACE TIMING SPECIFICAT	ONS				
FSMB	Bus Operating Frequency	(Note 12)	10		100	kHz
TBUF	Bus Free Time Between Stop and Start Condition		4.7			μs
THD:STA	Hold time after (Repeated) Start Condition. After this period, the first clock is generated.	At I _{PULLUP} , Max	4.0			μs
TSU:STA	Repeated Start Condition Setup Time		4.7			μs
TSU:STO	Stop Condition Setup Time		4.0			μs
THD:DAT	Data Hold Time		300			ns
TSU:DAT	Data Setup Time		250			ns
T _{TIMEOUT}	Detect Clock Low Timeout		25		35	ms
T _{LOW}	Clock Low Period		4.7			μs
T _{HIGH}	Clock High Period		4.0		50	μs
T _{LOW} :SEXT	Cumulative Clock Low Extend Time (Slave Device)				2	ms
t _F	Clock/Data Fall Time				300	ns
R	Clock/Data Rise Time				1000	ns
t _{POR}	Time in which a device must be operational after power-on reset				500	ms

Note 9: Recommended value. Parameter not tested in production.

Note 10: Recommended maximum capacitance load per bus segment is 400pF.

Note 11: Maximum termination voltage should be identical to the device supply voltage.

Note 12: Compliant to SMBus 2.0 physical layer specification. See System Management Bus (SMBus) Specification Version 2.0, section 3.1.1 SMBus common AC specifications for details.

Serial Management Bus (SMBus) Configuration Registers

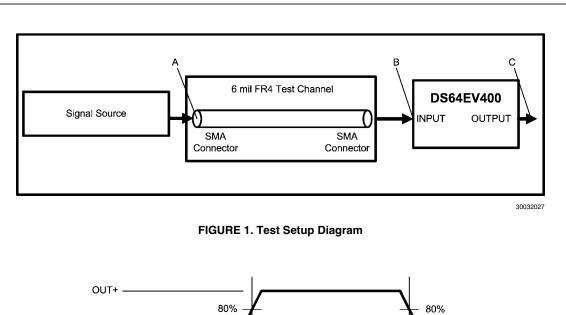
The Serial Management Bus interface is compatible to the SMBus 2.0 physical layer specification, except for bus termination voltages. Holding the CS pin high enables the SMBus

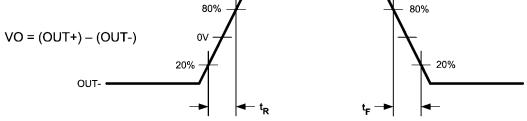
port allowing access to the SMBus registers. The configuration registers can be read and written using SMBus through the SDA and SDC pins. In the STANDBY state, the Searial Management Bus remains active. Please see Table 1 for more information.

Name	Address	Defaul t	Туре	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	
Status	0x00	0x00	RO	ID Revisio	n	1	1	SD3	SD2	SD1	SD0	
Status	0x01	0x00	RO	EN1	Boost 1			EN0	Boost 0			
Status	0x02	0x00	RO	EN3	Boost 3			EN2	Boost 2			
Enable/	0x03	0x44	RW	EN1	Boost C	ontrol		EN0	Boost C	Boost Control		
Boost				1: Enable	(BC for	CH1)		1: Enable		(BC for CH0)		
(BST_1,				0:	000 (Mii	n Boost)		0: Disable	000 (Mi	n Boost)	
BST_0)				Disable	001				001			
					010				010			
					011 100 (De	foult)			011	foult)		
					100 (De	iauit)			100 (De	naun)		
					110				110			
						x Boost)			111 (Ma	ax Boos	t)	
Enable/	0x04	0x44	RW	EN3	Boost C			EN2	Boost Control			
Boost				1: Enable					CH2)			
(BST_3,				0:	000 (Mii	n Boost)		0: Disable 000 (Min Boost) 001)	
BST_2)				Disable	001							
					010	010						
					011	foult)			011 100 (De	fourth)		
					100 (Default) 101 110				100 (De	iauii)		
								110				
						x Boost)			111 (Ma	ax Boos	t)	
Signal	0x05	0x00	RW	SD3 ON	· · ·	SD2 ON T	Threshold	SD1 ON Thr	reshold	SD0 C	N Threshold	
Detect				Threshold	Select	Select		Select		Select		
ON				00: 70 mV	,		/ (Default)	00: 70 mV			mV (Default)	
(SD_ON)				(Default)		01: 55 m\		(Default) 01:	: 55 mV	01: 55		
				01: 55 mV 10: 90 mV		10: 90 m\ 11: 75 m\		10: 90 mV 11: 75 mV		10: 90 11: 75		
				10. 90 mV 11: 75 mV		11.75 m	/	11.75 111		11.75	IIIV	
Signal	0x06	0x00	RW	SD3 OFF		SD2 OFF	Threshold	SD1 OFF Th	nreshold SD0 OFF Thresho)FF Threshold	
Detect	UNU UNU	onee		Threshold	Select	Select	Theorem	Select	liconola	Select		
OFF				00: 40 mV	,	00: 40 m\	/ (Default)	00: 40 mV (I	Default)	00: 40	mV (Default)	
(SD_OFF				(Default)		01: 30 m\	/	01: 30 mV		01: 30		
)				01: 30 mV		10: 55 m\		10: 55 mV		10: 55		
				10: 55 mV		11: 45 m\	/	11: 45 mV		11:45	mV	
OMD	007	000		11: 45 mV								
SMBus Control	0x07	0x00	RW	Reserved							SMBus Enable 0: Disable	
Control											1: Enable	
Output	0x08	0x78	RW	Reserved				Output Leve	l.	Reser		
Level	5,00							00: 400 mV _F				
								01: 540 mV _F				
								10: 620 mV _F				
								(Default)	•			
								11: 760 mV _p	р-р			

TABLE 1. SMBus Register Address

Note: RO = Read Only, RW = Read/Write





30032002

FIGURE 2. CML Output Transition Times

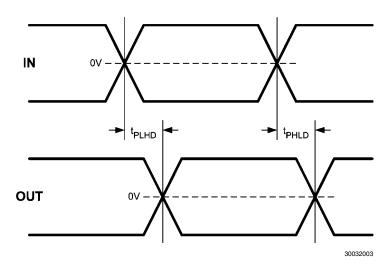
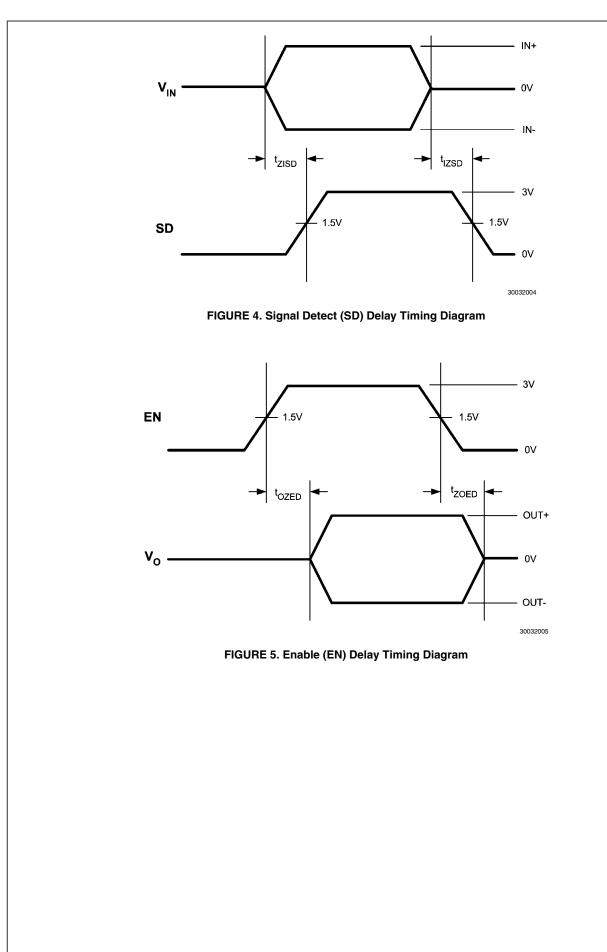


FIGURE 3. Propagation Delay Timing Diagram



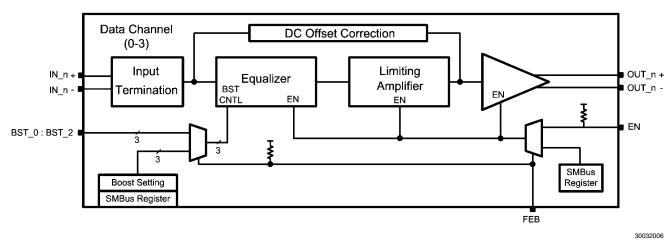


DS64EV400 Applications Information

The DS64EV400 is a programmable quad equalizer optimized for operation up to 10 Gbps for backplane and cable applications.

DATA CHANNELS

The DS64EV400 provides four data channels. Each data channel consists of an equalizer stage, a limiting amplifier, a DC offset correction block, and a CML driver as shown in Figure 6.





EQUALIZER BOOST CONTROL

Each data channel support eight programmable levels of equalization boost. The state of the FEB pin determines how the boost settings are controlled. If the FEB pin is held High, then the equalizer boost setting is controlled by the Boost Set pins (BST_[2:0]) in accordance with Table 2. If this programming method is chosen, then the boost setting selected on the Boost Set pins is applied to all channels. When the FEB pin is held Low, the equalizer boost level is controlled through the SMBus. This programming method is accessed via the appropriate SMBus registers (see Table 1). Using this approach, equalizer boost settings can be programmed for each channel individually. FEB is internally pulled High (default setting); therefore if left unconnected, the boost settings are controlled by the Boost Set pins (BST_[0:2]). The eight levels of boost settings enables the DS64EV400 to address a wide range of media loss and data rates.

6 mil Microstri p FR4 Trace	24 AWGChannelChannel[BST_2,Twin-AXLoss atLoss at 5BST_1,cable3.2 GHzGHz (dB)BST_0]length (m)(dB)Image: Comparison of the second			
Length (m)	_ 、 /			
0	0	0	0	000
5	2	5	6	001
10	3	7.5	10	010
15	4	10	14	011
20	5	12.5	18	1 0 0 (Default)
25	6	15	21	101
30	7	17	24	110
40	10	22	30	111

DEVICE STATE AND ENABLE CONTROL

The DS64EV400 has an Enable feature on each data channel which provides the ability to control device power consumption. This feature can be controlled either via each Enable Pin (ENn Pin) or via the Enable Control Bit which is accessed through the SMBus port (see Table 1 and Table 3). If the Enable is activated, the corresponding data channel is placed in the ACTIVE state and all device blocks function as described. The DS64EV400 can also be placed in STANDBY mode to save power. In this mode only the control interface including the SMBus port, as well as the signal detection circuit remain active.

TABLE 3.	Controlling	Device	State
	o o na o na g	D 01100	outo

Register 07[0] (SMBus)	ENn Pin (CMOS)	Channel 0: Register 03[3] Channel 1: Register 03[7] Channel 2: Register 04[3] Channel 3: Register 04[7] (EN Control) (SMBus)	Device State
0 : Disable	1	Х	ACTIVE
0 : Disable	0	Х	STANDBY
1 : Enable	Х	0	ACTIVE
1 : Enable	Х	1	STANDBY

SIGNAL DETECT

The DS64EV400 features a signal detect circuit on each data channel. The status of the signal of each channel can be determined by either reading the Signal Detect bit (SDn) in the SMBus registers (see Table 1) or by the state of each SDn pin. A logic High indicates the presence of a signal that has exceeded a specified maximum threshold value (called

SD_ON). A logic Low means that the input signal has fallen below a minimum threshold value (called SD_OFF). These values are programmed via the SMBus (Table 1). If not programmed via the SMBus, the minimum and maximum thresholds take on the default values for the minimum and maximum values as indicated in Table 4. The Signal Detect threshold values can be changed through the SMBus. All threshold values specified are DC peak-to-peak differential signals (positive signal minus negative signal) at the input of the device.

TABLE 4	. Signal	Detect	Threshold	Values
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Channel 0: Bit 1 Channel 1: Bit 3 Channel 2: Bit 5 Channel 3: Bit 7	Channel 0: Bit 0 Channel 1: Bit 2 Channel 2: Bit 4 Channel 3: Bit 6	Minimum Threshold Register 06 (mV)	Maximum Threshold Register 05 (mV)
0	0	40 (Default)	70 (Default)
0	1	30	55
1	0	55	90
1	1	45	75

OUTPUT LEVEL CONTROL

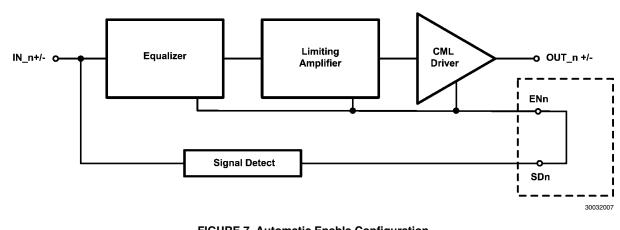
The output amplitude of the CML drivers for each channel can be controlled via the SMBus (see Table 1). The default output level is 650 mV_{p-p}. The following Table presents the output level values supported:

TABLE 5. Output Level Control Settings

All Channels : Bit 3	All Channels : Bit 2	Output Level Register 08 (mV _{P-P})
0	0	400
0	1	540
1	0	620 (Default)
1	1	760

AUTOMATIC ENABLE FEATURE

It may be desirable to place unused channels in power-saving Standby mode. This can be accomplished by connecting the Signal detect (SDn) pin to the Enable (ENn) pin for each channel (See Figure 7). In order for this option to function properly, the FEB pin must be either tied High or not connected (the FEB pin is internally pulled High by default). If an input signal swing applied to a data channel is above the maximum level specified in the threshold register via the SMBus, then the SDn pin is asserted High. If the SDn pin is connected to the ENn pin, this will enable the equalizer, limiting amplifier, and output buffer on the data channels (provided that the FEB pin is High); thus the DS64EV400 will automatically enter the ACTIVE state. If the input signal swing falls below the minimum level specified in the threshold register, then the SDn pin will be asserted Low, causing the aforementioned blocks to be placed in the STANDBY state.





UNUSED EQUALIZER CHANNELS

It is recommended to put all unused channels into standby mode.

GENERAL RECOMMENDATIONS

The DS64EV400 is a high performance circuit capable of delivering excellent performance. Careful attention must be paid to the details associated with high-speed design as well as providing a clean power supply. Refer to the LVDS Owner's Manual for more detailed information on high-speed design tips to address signal integrity design issues.

PCB LAYOUT CONSIDERATIONS FOR DIFFERENTIAL PAIRS

The CML inputs and outputs must have a controlled differential impedance of 100 $\!\Omega.$ It is preferable to route CML lines

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exclusively on one layer of the board, particularly for the input traces. The use of vias should be avoided if possible. If vias must be used, they should be used sparingly and must be placed symmetrically for each side of a given differential pair. Route the CML signals away from other signals and noise sources on the printed circuit board. See AN-1187 for additional information on LLP packages.

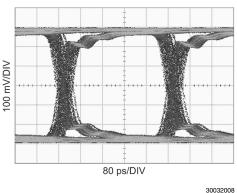
POWER SUPPLY BYPASSING

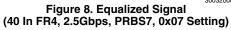
Two approaches are recommended to ensure that the DS64EV400 is provided with an adequate power supply. First, the supply (V_{DD}) and ground (GND) pins should be connected to power planes routed on adjacent layers of the printed circuit board. The layer thickness of the dielectric should be minimized so that the V_{DD} and GND planes create a low inductance supply with distributed capacitance. Sec-

ond, careful attention to supply bypassing through the proper use of bypass capacitors is required. A 0.01 μ F bypass capacitor should be connected to each V_{DD} pin such that the capacitor is placed as close as possible to the DS64EV400. Smaller body size capacitors can help facilitate proper component placement. Additionally, three capacitors with capacitance in the range of 2.2 μ F to 10 μ F should be incorporated in the power supply bypassing design as well. These capacitors can be either tantalum or an ultra-low ESR ceramic and should be placed as close as possible to the DS64EV400.

DS64EV400

Typical Performance Eye Diagrams and Curves





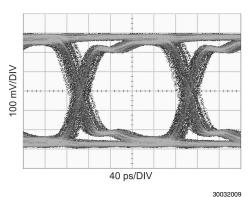


Figure 9. Equalized Signal (40 In FR4, 5Gbps, PRBS7, 0x07 Setting)

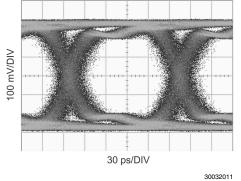


Figure 11. Equalized Signal (40 In FR4, 6.4 Gbps, PRBS31, 0x06 Setting)

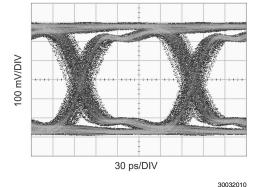
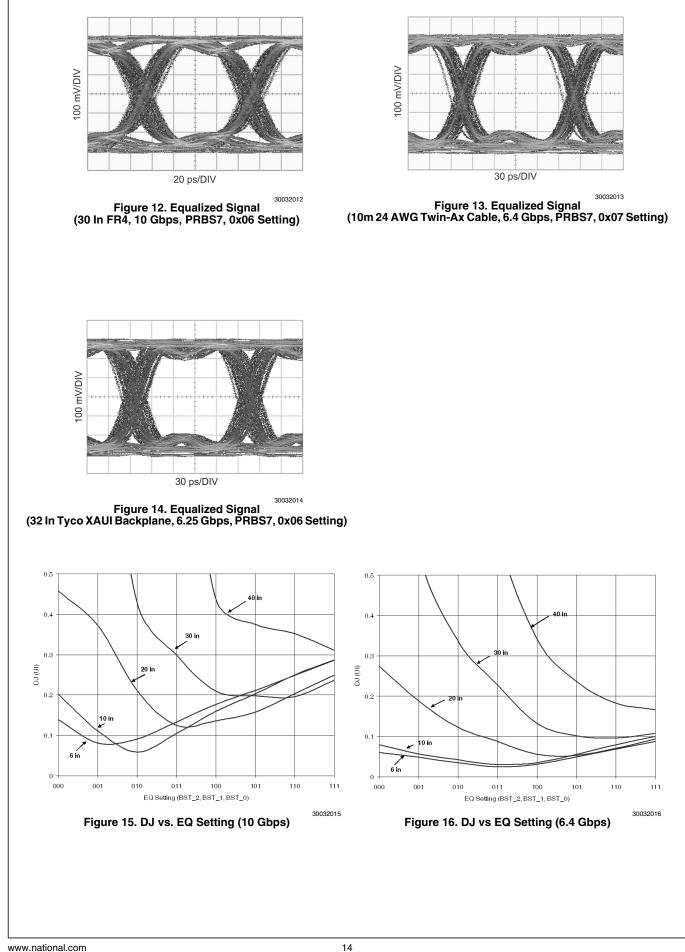
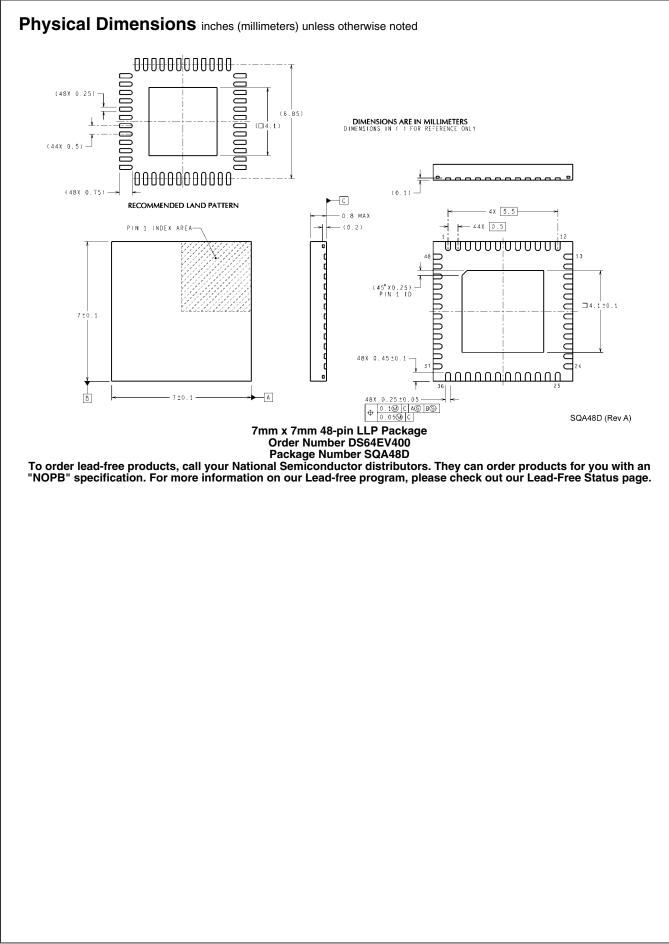


Figure 10. Equalized Signal (40 In FR4, 6.4 Gbps, PRBS7, 0x06 Setting)







Notes

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